

What is claimed is:

1. A method for vacuum-mounting at least one micro electro

mechanical system (MEMS) on a substrate, comprising:

attaching a getter to an interior surface of a cavity formed on a cover;

aligning the cover and a semiconductor substrate in a vacuum

chamber;

injecting an inert gas into the vacuum chamber to achieve a

predetermined degree of vacuum; and

bonding the cover and the semiconductor substrate.

2. The method as claimed in claim 1, wherein the getter is

substantially made of titanium.

3. The method as claimed in claim 1, wherein the bonding is

performed after a predetermined time has lapsed after the injection of the

inert gas.

4. The method as claimed in claim 1, wherein the inert gas is argon gas.

5. The method as claimed in claim 1, further comprising: discharging the inert gas to adjust the degree of vacuum in the vacuum chamber if an excessive amount of inert gas is injected into the vacuum chamber.

6. The method as claimed in claim 1, wherein aligning the cover and the semiconductor substrate in a vacuum chamber comprises: adjusting a supporting means for supporting the cover and the semiconductor substrate in a vacuum chamber; and adjusting a transporting means for transporting the cover and the semiconductor substrate in a vacuum chamber.

7. The method as claimed in claim 1, wherein the bonding is anodic bonding.

8. The method as claimed in claim 1, wherein bonding the cover and the semiconductor substrate comprises:

heating the cover to a predetermined temperature; and

applying a high voltage to the cover.

9. An apparatus for vacuum-mounting at least one micro electro mechanical system (MEMS), comprising:

a gas injecting section for injecting an inert gas into a vacuum chamber;

a substrate aligning section for aligning a semiconductor substrate and a cover, the cover having a cavity formed therein and a getter attached to an interior surface of the cavity;

a bonding section for bonding the semiconductor substrate and the cover together; and

a controlling section for controlling the substrate aligning section to align the semiconductor and the cover, for controlling the gas injecting section to inject the inert gas into the vacuum chamber, and for controlling

the bonding section to bond the semiconductor substrate and the cover together after the inert gas is injected.

10. The apparatus as claimed in claim 9, wherein the substrate aligning section comprises:

a supporting means for supporting both the semiconductor substrate and the cover; and

a transporting means for transporting both the semiconductor substrate and the cover.

11. The apparatus as claimed in claim 9, wherein the bonding section comprises:

a heat supplying part for applying a predetermined amount of heat to the cover; and

a high voltage supplying part for supplying a high voltage to the cover, wherein the controlling section controls the heat supplying part and the high voltage supplying part according to a preset bonding condition.

12. The apparatus as claimed in claim 9, wherein the controlling section controls the bonding section to bond the semiconductor substrate and the cover to be bonded together after a predetermined time has lapsed after the inert gas is injected.

13. The apparatus as claimed in claim 9, wherein the getter is substantially made of titanium.

14. The apparatus as claimed in claim 9, wherein the inert gas is argon gas.

15. The apparatus as claimed in claim 9, further comprising: a gas discharging section for discharging the inert gas from the vacuum chamber to adjust a degree of vacuum in the vacuum chamber.

16. The apparatus as claimed in claim 9, wherein the cover is a glass plate.